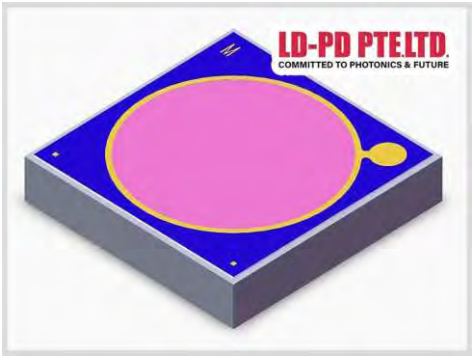
Large Area InGaAs/InP PIN Photodiode Chip



Description

LD-PD's InGaAs pin structure based on InP by MOCVD method and planar diffusing technology. The sensitive areas of TO photodiode series products are φ5mm、φ10mm、φ15mm respectively. The products with other sensitive area, shape or package style can also be provided according to the demand of users.

Features

- 10mm Active diameters
- High responsivity
- Low capacitance
- Low dark current
- High shunt resistance

Specifications

Specification (Tc=25℃)

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions
Response range	λ	900		1650	nm	
Responsivity	R	0.85	0.90		A/W	λ= 1310nm
			0.95			λ= 1550nm
			0.2			λ=850nm
Dark current	ID		15	100	nA	VR=-2V
Capacitance	C		12		nF	VR=0V, f= 1MHz

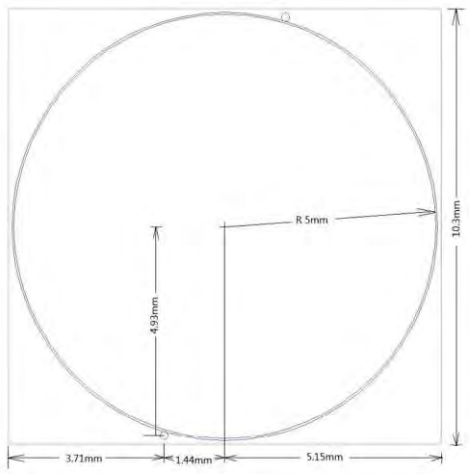
Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Reverse voltage	VRmax	5	V
Forward Current		10	mA
Operating temperature	Topr	-40 to +85	℃
Storage temperature	Tstg	-55 to +125	℃

Dimension Parameter

Parameter	Symbol	Value	Unit
Active area diameter	D	10	mm
Bond pad diameter	-	200	μm
Die size	-	10300*10300	μm
Die thickness	t	200±20	μm

Dimension



Application

- Monitoring
- Fiber-optic Instruments
- Data Communications